

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 3

## **Maximum Ratings**

• Operating Junction Temperature Range : -55°C to +150°C

• Storage Temperature Range: -55°C to +150°C

• Thermal Resistance: 2.1°C/W Junction to Case<sup>(2)</sup>

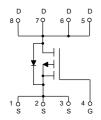
• Thermal Resistance: 123°C/W Junction to Ambient(2)

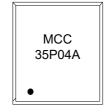
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	-40	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-35	Α
Pulsed Drain Current <sup>(3)</sup>	I <sub>DM</sub>	-140	Α
Total Power Dissipation	P <sub>D</sub>	59	W
Single Pulsed Avalanche Energy <sup>(4)</sup>	E <sub>AS</sub>	108	mJ

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The Value of  $R_{\theta JA}$  is Measured with the Device Mounted on 1in2 FR-4 Board with 2oz. Copper, in a Still Air Environment with  $T_A$ =25°C. The Value in Any Given Application Depends on the User's Specific Board Design.
- 3. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.
- 4.  $V_{DS}$ =-35V,  $V_{GS}$ =-10V, L=1mH,  $I_{AS}$ =-14.7A.

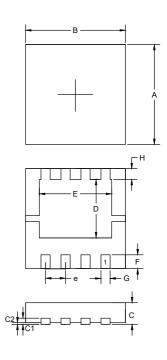
## **Internal Structure and Marking Code**





# P-CHANNEL MOSFET

#### **DFN3333**



DIMENSIONS					
DIM	INC	HES	MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.126	0.130	3.20	3.30	
В	0.126	0.130	3.20	3.30	
С	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2		0.002		0.05	
D	0.071	0.079	1.80	2.00	
Е	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
Н	0.012	0.016	0.30	0.40	
е	0.024	0.028	0.60	0.70	

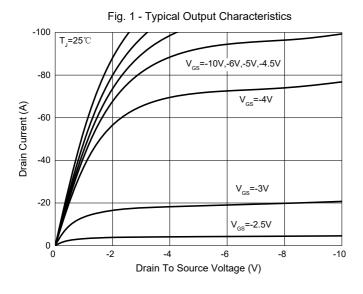


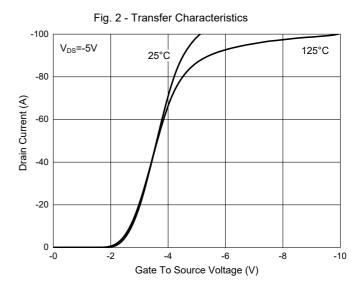
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

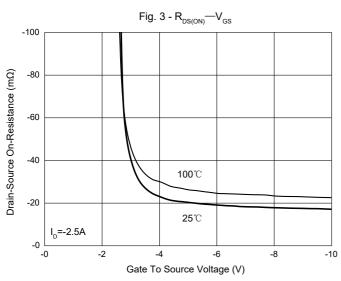
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			<u>'</u>			1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-40			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1	-1.6	-2.5	V	
Dunin Course On Basistan	В	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		16	20	mΩ	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		20	25		
Diode Characteristics				1	I.	1	
Continuous Body Diode Current	Is				-35	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.2	V	
Reverse Recovery Time	t <sub>rr</sub>			21.5		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-17A, dI <sub>F</sub> /dt=100A/μs		8		nC	
Dynamic Characteristics	-		,	1		1	
Input Capacitance	C <sub>iss</sub>			2511			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-25V,V <sub>GS</sub> =0V,f=1MHz		174		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			158			
Total Gate Charge	$Q_g$			57			
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-20V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-3A		9.5		nC	
Gate-Drain Charge	$Q_{gd}$			9.8			
Turn-On Delay Time	t <sub>d(on)</sub>			7.3			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V,		22.6		-	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=6\Omega$ , $I_{DS}=-3A$		160		ns	
Turn-Off Fall Time	t <sub>f</sub>			53			

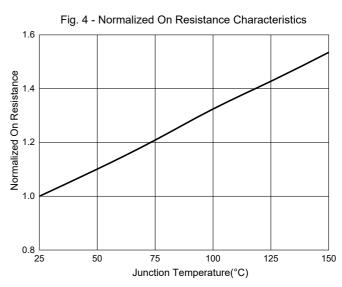


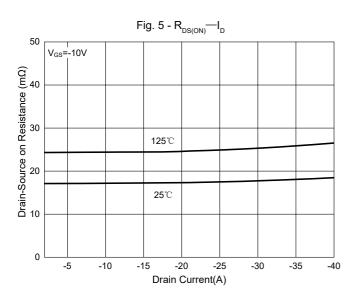
#### **Curve Characteristics**

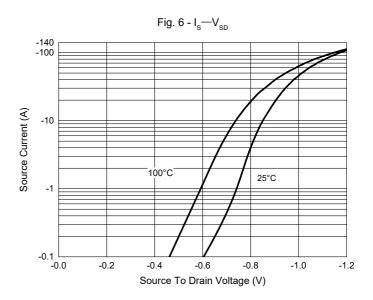






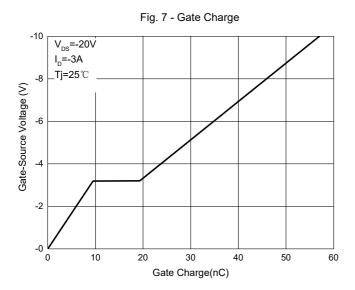


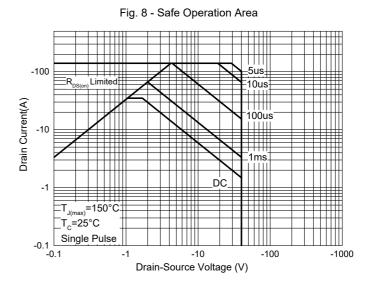


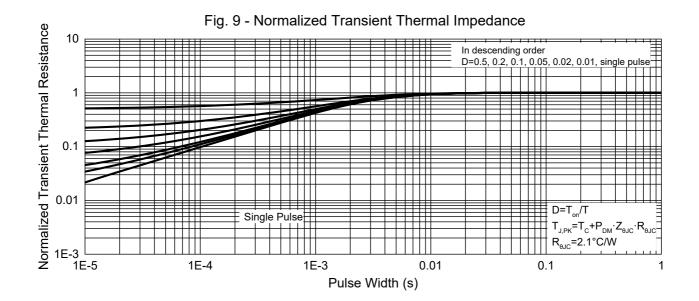




#### **Curve Characteristics**









### **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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